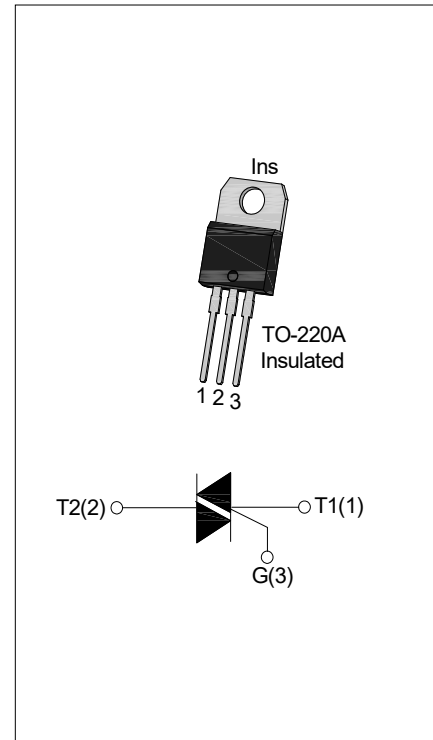




### DESCRIPTION:

With high ability to withstand the shock loading of large current, JST24A-1200BW triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, especially recommended focus on inductive load. From all three terminals to external heatsink, JST24A-1200BW provide a rated insulation voltage of 2500 V<sub>RMS</sub>, complying with UL standards (File ref: E252906). Packages TO-220A is RoHS compliant. (2011/65/EU)



### MAIN FEATURES

Symbol	Value	Unit
I <sub>T(RMS)</sub>	25	A
V <sub>DRM</sub> / V <sub>R<sub>RM</sub></sub>	1200	V

### ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T <sub>stg</sub>	-40-150	°C
Operating junction temperature range		T <sub>j</sub>	-40-125	°C
Repetitive peak off-state voltage (T <sub>j</sub> =25°C)		V <sub>DRM</sub>	1200	V
Repetitive peak reverse voltage (T <sub>j</sub> =25°C)		V <sub>R<sub>RM</sub></sub>	1200	V
RMS on-state current	TO-220A(Ins) (T <sub>C</sub> =70°C)	I <sub>T(RMS)</sub>	25	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I <sub>TSM</sub>	250	A
I <sup>2</sup> t value for fusing (tp=10ms)		I <sup>2</sup> t	340	A <sup>2</sup> s
Critical rate of rise of on-state current (I <sub>G</sub> = 2 × I <sub>GT</sub> )		di/dt	50	A/μs
Peak gate current		I <sub>GM</sub>	4	A
Average gate power dissipation		P <sub>G(AV)</sub>	1	W
Peak gate power		P <sub>GM</sub>	10	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX	50	mA
$V_{GT}$		I - II -III	MAX	1.3	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX	80	mA
		II		100	
$I_H$	$I_T=100\text{mA}$		MAX	75	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	1000	V/ $\mu\text{s}$

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=35\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.95	V
$R_d$	Dynamic resistance	$T_j=125^\circ\text{C}$	13	$\text{m}\Omega$
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	3	mA

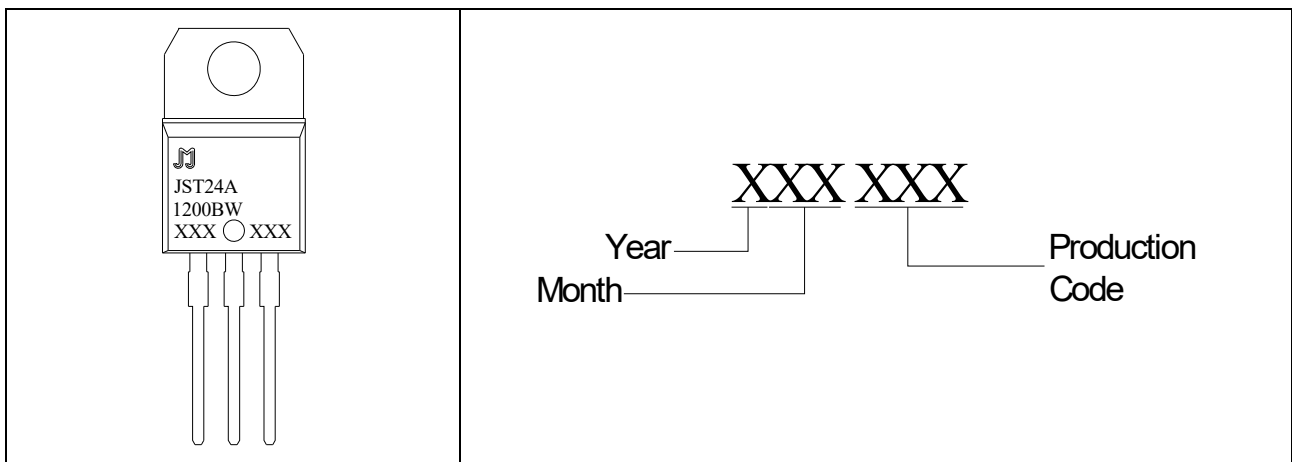
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	1.5	$^\circ\text{C}/\text{W}$

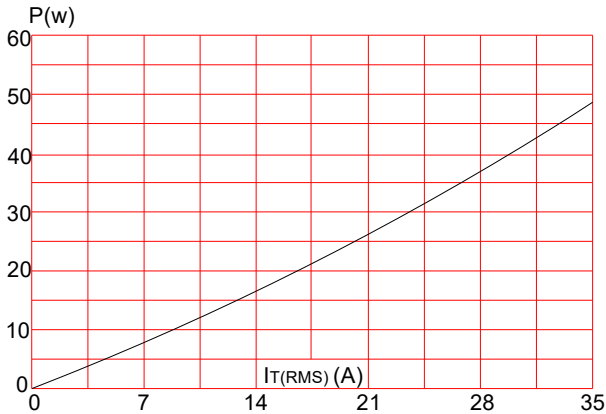
**ORDERING INFORMATION**

J	ST	24	A	-1200	BW	- /
JieJie Microelectronics Co.,Ltd	Triacs IT(RMS):25A		A:TO-220A(Ins)		BW:IGT1-3≤50mA	Blank: Tube
				1200:VDRM /VRRM≥1200V		

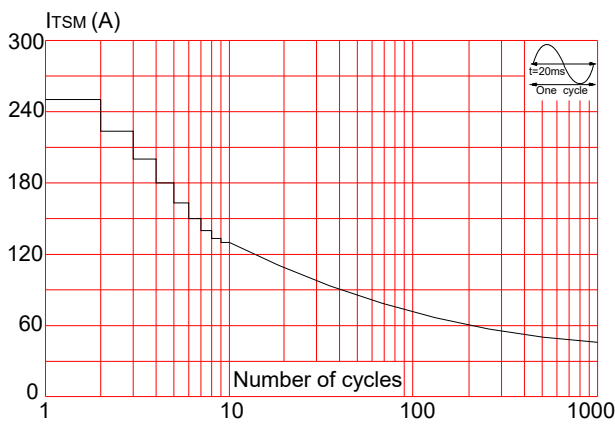
**MARKING**



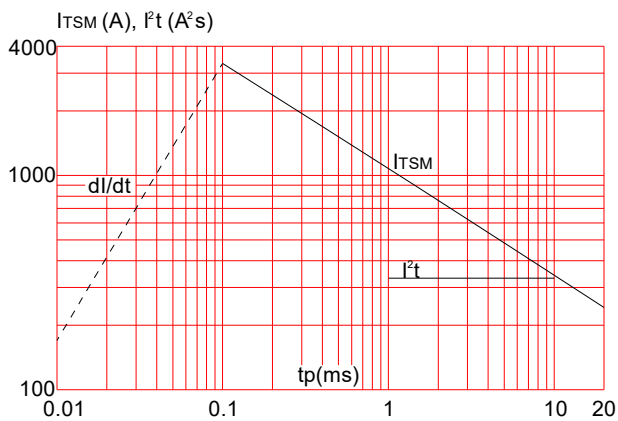
**FIG.1:** Maximum power dissipation versus RMS on-state current



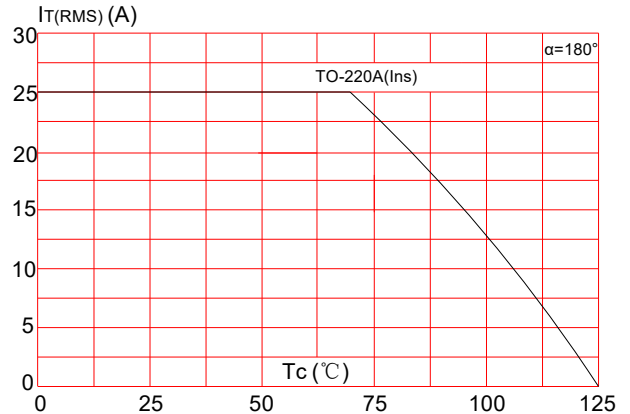
**FIG.3:** Surge peak on-state current versus number of cycles



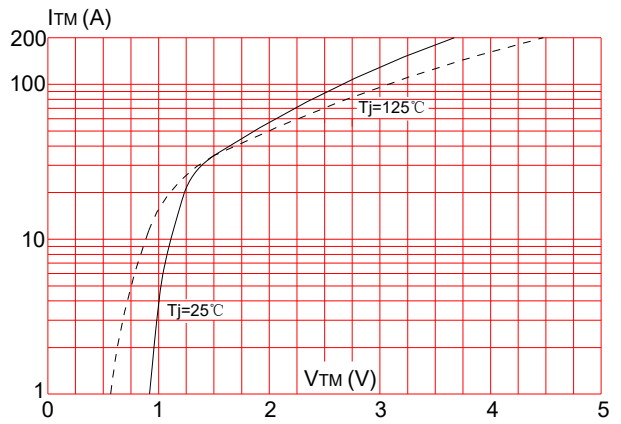
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )



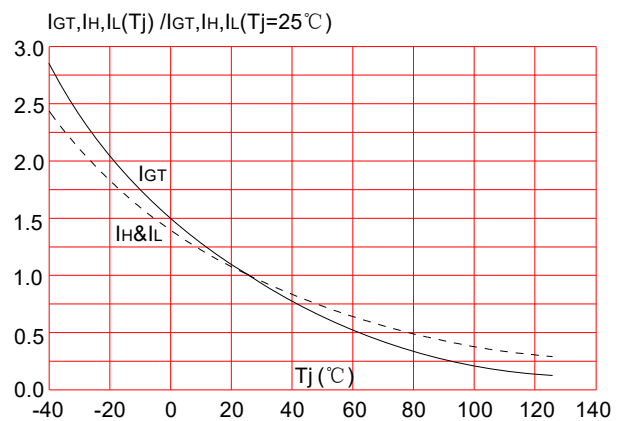
**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



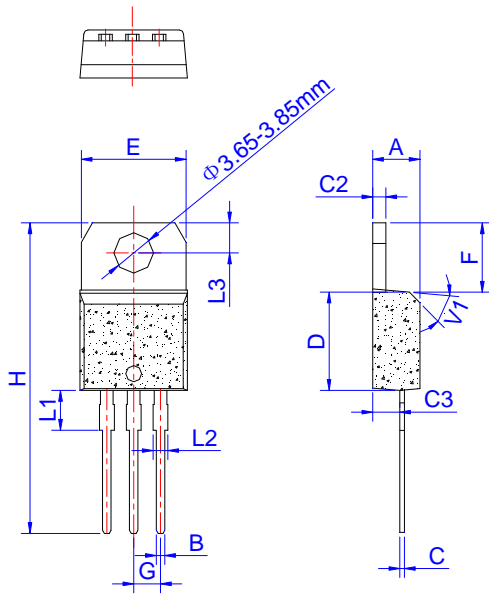
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST24A-1200BW	1200	50	TO-220A(Ins)	50	Tube

**Document Revision History**

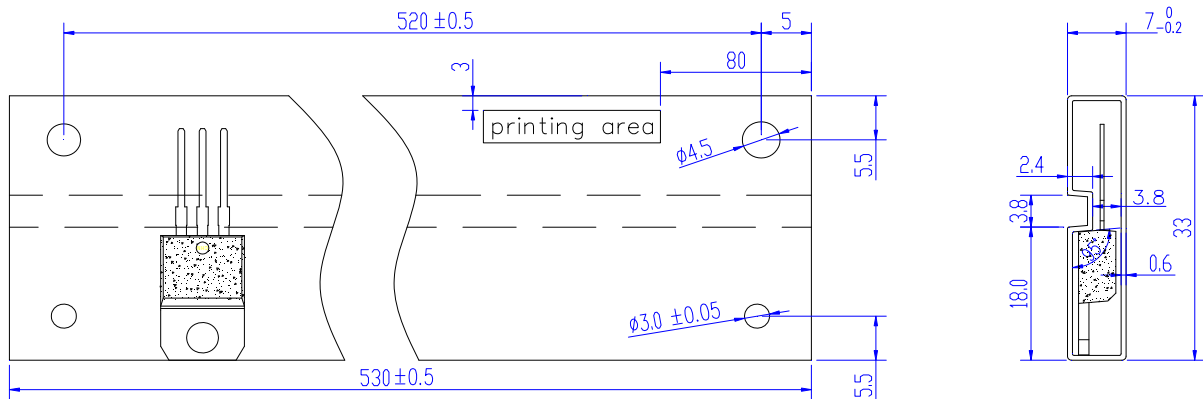
Date	Revision	Changes
Mar 22, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000



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